

2SC3236

SILICON NPN TRIPLE DIFFUSED TYPE

SWITCHING REGULATOR AND HIGH VOLTAGE SWITCHING APPLICATIONS.

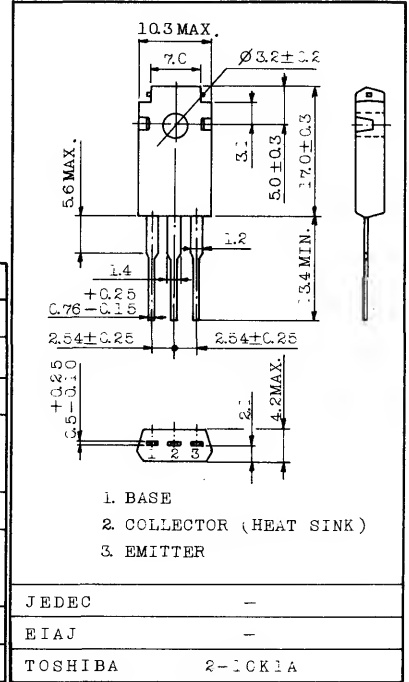
HIGH SPEED DC-DC CONVERTER APPLICATION.

FEATURES:

- Excellent Switching Times
: $t_r=1.0\mu s(\text{Max.})$, $t_f=1.0\mu s(\text{Max.})$ at $I_C=4A$
- High Collector Breakdown Voltage : $V_{CEO}=400V$

INDUSTRIAL APPLICATIONS

Unit in mm



MAXIMUM RATINGS ($T_a=25^\circ C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	500	V
Collector-Emitter Voltage		V_{CEO}	400	V
Emitter-Base Voltage		V_{EBO}	7	V
Collector Current	DC	I_C	5	A
	Pulse	I_{CP}	7	A
Base Current		I_B	1	A
Collector Power Dissipation	$T_a=25^\circ C$	P_C	1.7	W
	$T_c=25^\circ C$		60	
Junction Temperature		T_j	150	$^\circ C$
Storage Temperature Range		T_{stg}	-55 ~ 150	$^\circ C$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Collector Cut-off Current	I_{CBO}	$V_{CB}=400V, I_E=0$	-	-	100	μA	
Emitter Cut-off Current	I_{EBO}	$V_{EB}=7V, I_C=0$	-	-	1	mA	
Collector-Base Breakdown Voltage	$V(BR)_{CBO}$	$I_C=1mA, I_E=0$	500	-	-	V	
Collector-Emitter Breakdown Voltage	$V(BR)_{CEO}$	$I_C=10mA, I_B=0$	400	-	-	V	
DC Current Gain	h_{FE}	$V_{CE}=5V, I_C=3A$	12	-	-		
		$V_{CE}=5V, I_C=5A$	8	-	-		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=5A, I_B=1A$	-	-	1.0	V	
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=5A, I_B=1A$	-	-	1.5	V	
Switching Time	Rise Time	t_r			-	1.0	μs
	Storage Time	t_{stg}			-	2.5	
	Fall Time	t_f			-	1.0	

TOSHIBA CORPORATION

SWITCHING CHARACTERISTICS

